

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-60V	90mΩ@-10V	-3A
	100mΩ@-4.5V	

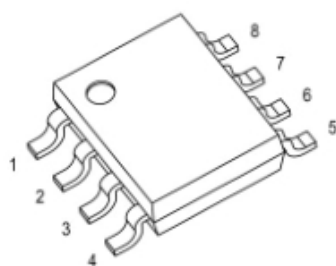
Feature

- $R_{DS(on)} \leq 105m\Omega$ at $V_{GS} = -10V$, $I_D = -3A$
- $R_{DS(on)} \leq 135m\Omega$ at $V_{GS} = -4.5V$, $I_D = -2.5A$
- RoHS Compliant

Application

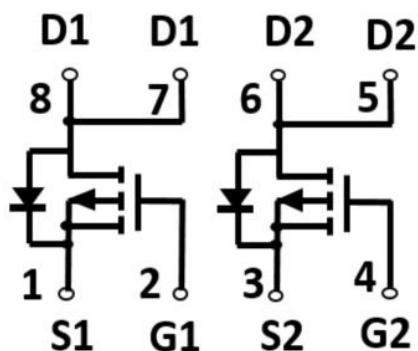
- Load Switch
- Power Management

Package

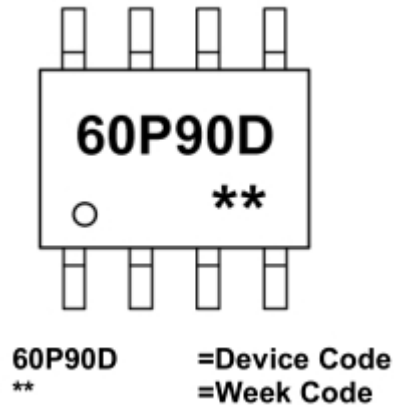


SOP-8L

Circuit diagram



Marking



Absolute maximum ratings

(T_a=25°C unless otherwise noted)

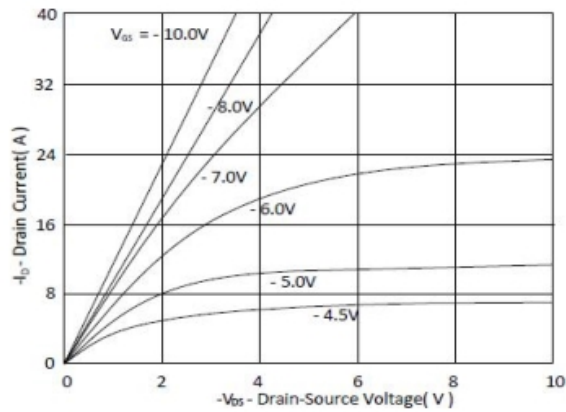
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	-60	V
Gate-Source Voltage	V _{GS}	±20	V
Continuous Drain Current(T _c =25°C)	I _D	-3	A
Pulsed Drain Current	I _{DM}	-12	A
Maximum Power Dissipation (T _a =25°C)	P _D	2	W
Thermal Resistance Junction-Case	R _{θJC}	78	°C/W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

Electrical characteristics

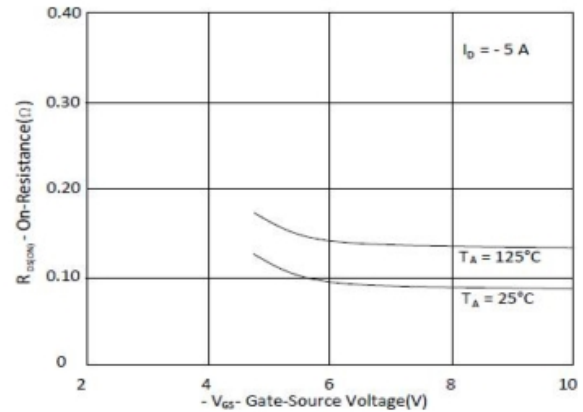
($T_A=25^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV (BR)DSS	V _{GS} = 0V, I _D = -250μA	-60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -60V, V _{GS} = 0V			-1	uA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	uA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1	-1.5	-2.5	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = -10V, I _D = -3A		90	105	mΩ
		V _{GS} = -4.5V, I _D = -2.5A		100	135	
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} = -25V, V _{GS} =0V, f=1MHz		963		pF
Output Capacitance	C _{oss}			96		
Reverse Transfer Capacitance	C _{rss}			71		
Switching Characteristics						
Turn-on Delay Time	T _{d(on)}	V _{DD} = -10V, I _D = -1A, V _{GS} = -10V, R _G = 6Ω		8		nS
Turn-on Rise Time	T _r			12		
Turn-off Delay Time	T _{d(off)}			20		
Turn-off Fall Time	T _f			12		
Total Gate Charge (4.5V)	Q _g	V _{DD} = -30V, I _D = -10A, V _{GS} = -10V		16.2		nC
Gate-Source Charge	Q _{gs}			2.0		
Gate-Drain Charge	Q _{gd}			3.5		
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	I _{SD} = -10A, V _{GS} = 0V			-1.3	V

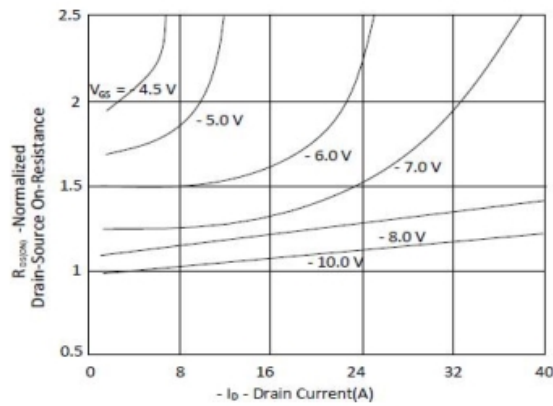
Typical Characteristics



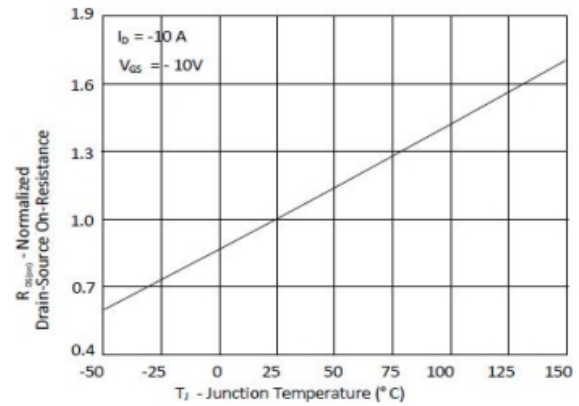
Typical Output Characteristics



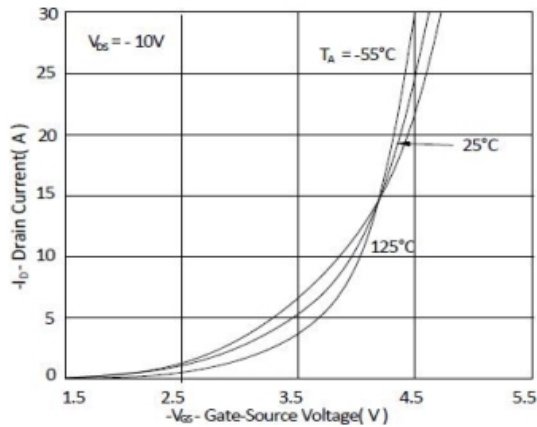
On-Resistance vs. Gate-Source Voltage



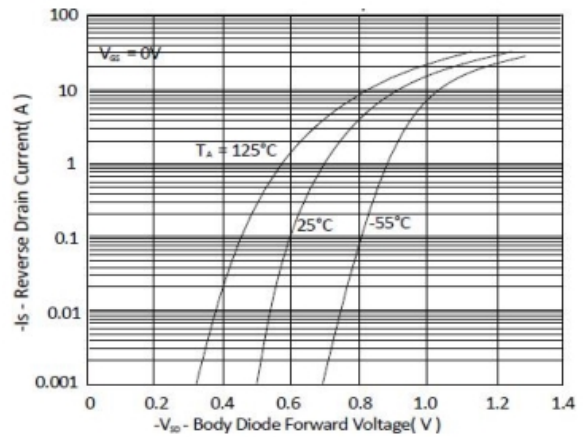
On-Resistance vs. Drain Current and Gate Voltage



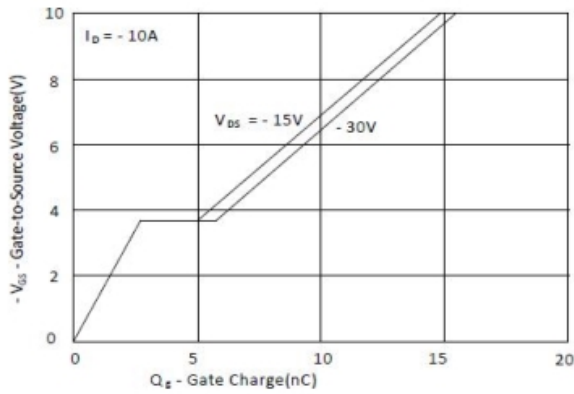
Normalized On-Resistance vs. Junction Temperature



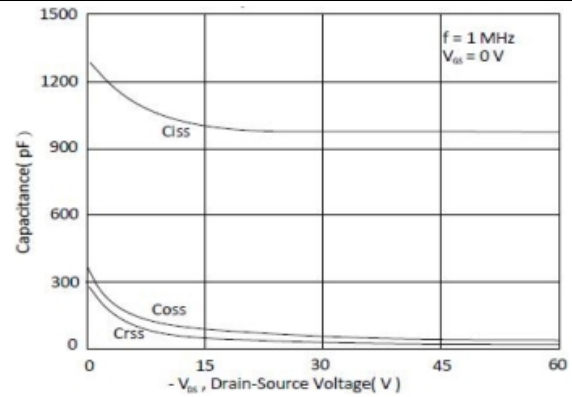
Typical Transfer Characteristics



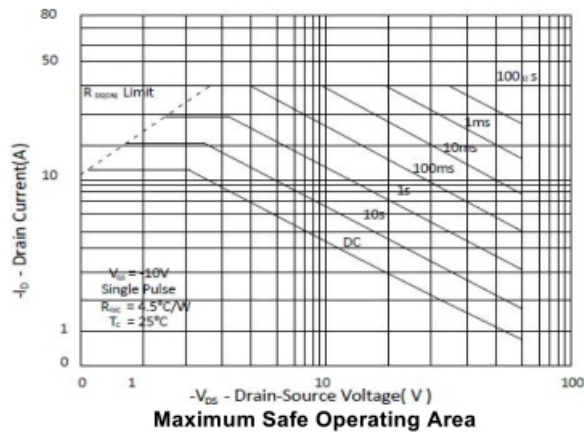
Typical Source-Drain Diode Forward Voltage



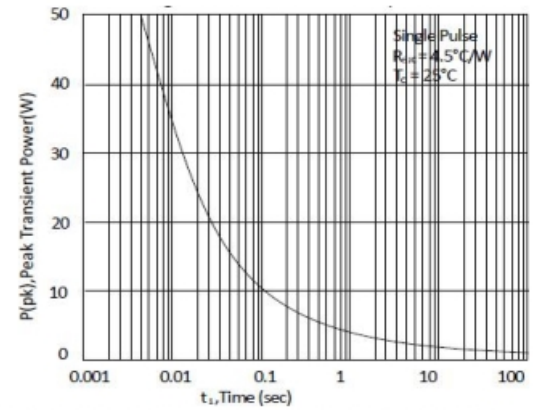
Typical Gate-Charge vs. Gate-to-Source Voltage



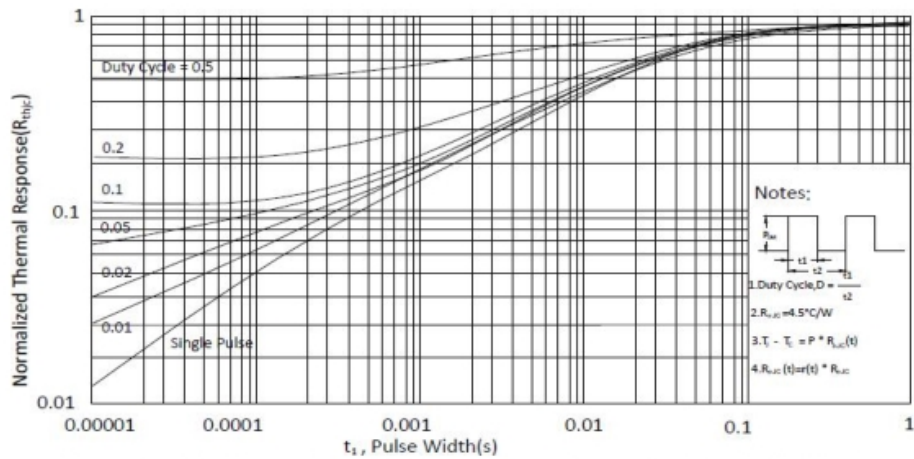
Typical Capacitance vs. Drain-to-Source Voltage



Maximum Safe Operating Area

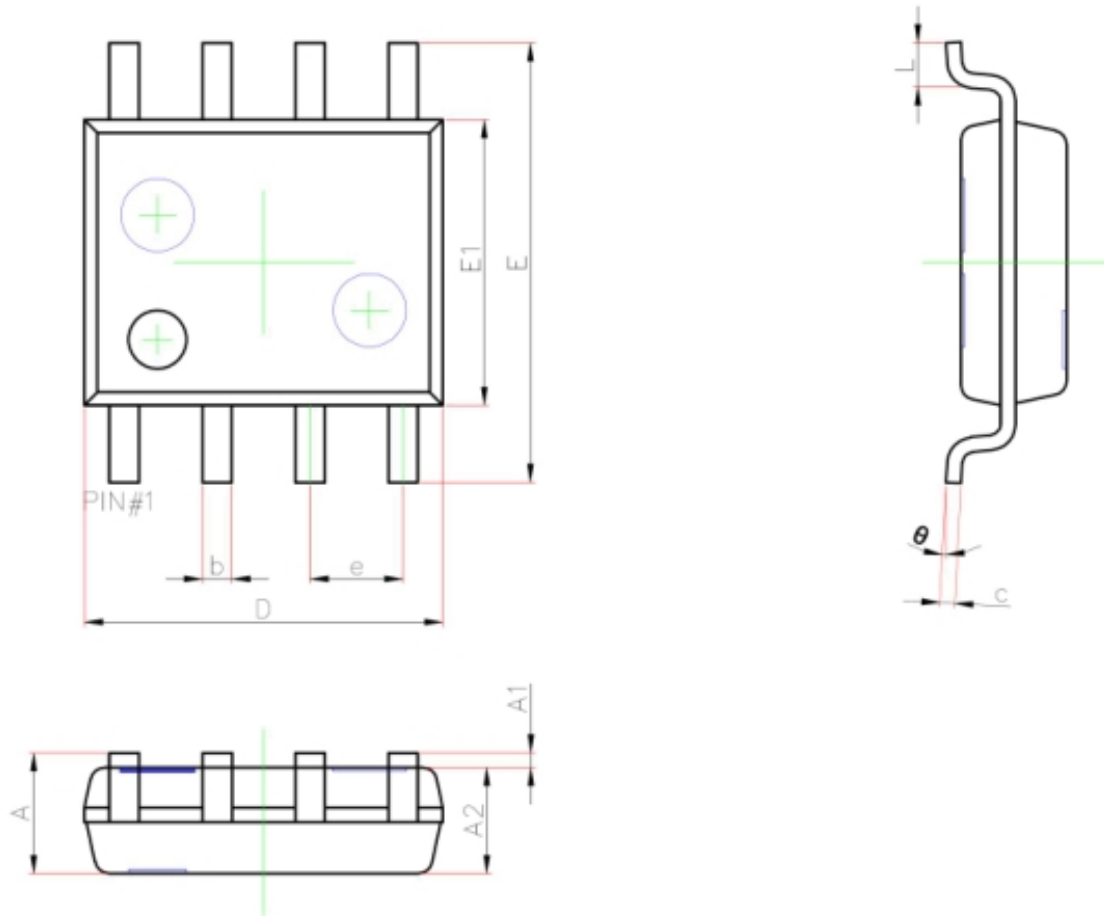


Maximum Drain Current vs. Case Temperature



Normalized Maximum Transient Thermal Impedance, Junction-to-Ambient

SOP-8L Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	1.35	1.75
A1	0.10	0.25
A2	1.35	1.55
b	0.33	0.51
c	0.17	0.25
D	4.80	5.00
e	1.27 REF.	
E	5.80	6.20
E1	3.80	4.00
L	0.40	1.27
θ	0°	8°